



Microsemi Extends Its New Radiation Hardened Transistor Product Line

Adds 54 Products for Aerospace, Defense, Satellite Applications

IRVINE, Calif., Sep 8, 2009 (GlobeNewswire via COMTEX News Network) -- Microsemi Corporation (Nasdaq:MSCC), a leading manufacturer of high performance analog/mixed signal integrated circuits and high reliability semiconductors, announced today that DSCC qualification has been granted on their JANSR2N3439 and JANSR2N3440 radiation hardened medium power transistors.

With these latest approvals Microsemi has now qualified an additional 54 radiation hardened transistor products over the last year. This includes 44 new packaged device types and 10 newly-qualified radiation hardened die types for hybrid packaging applications.

These general purpose, small signal and medium power bipolar transistors are primarily used in aerospace, defense and satellite communication applications. They are specifically designed to perform in the severe environmental and radiation conditions that exist in space where component selection is essential to mission success.

Microsemi has worked closely with the Defense Supply Center Columbus (DSCC) to define the test specifications within standard military drawings (MIL-PRF-19500 slashsheets) so that customers can be assured of the radiation performance capabilities of these products.

Features include:

- * NPN & PNP
- * Low and medium power
- * Standard hermetic package outlines in both through-hole and surface mount configurations
- * Radiation Hardened for Total Ionizing Dose performance of 100,000 (R) and 300,00 (F) RAD(Si) as shown below
- * Space level Quality

The new product qualifications include:

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Microsemi Part Number	Pt @Ta=25C	Vcbo	Vceo	Ic	Polarity	Package	MIL-PRF-19500
JANSR2N2218	800mW	60V	30V	800mA	NPN	T0-39	/251
JANSR2N2218A	800mW	75V	50V	800mA	NPN	T0-39	/251
JANSR2N2218AL	800mW	75V	50V	800mA	NPN	T0-5	/251
JANSR2N2219	800mW	60V	30V	800mA	NPN	T0-39	/251
JANSR2N2219A	800mW	75V	50V	800mA	NPN	T0-39	/251
JANSR2N2219AL	800mW	75V	30V	800mA	NPN	T0-5	/251
JANSR2N2369A	360mW	40V	15V	30mA	NPN	T0-18	/317
JANSF2N2369AU	500mW	40V	15V	30mA	NPN-Dual	U	/317
JANSF2N2369AUA	360mW	40V	15V	30mA	NPN	UA	/317
JANSF2N2369AUB	360mW	40V	15V	30mA	NPN	UB	/317
JANKCAF2N2369A	360mW	40V	15V	30mA	NPN	Die	/317
JANSF2N4449	360mW	40V	15V	30mA	NPN	T0-46	/317

JANSR2N3700	500mW	140V	80V	1A	NPN	T0-39	/391
JANSR2N3700UB	500mW	140V	80V	1A	NPN	UB	/391
JANKCBR2N3700	500mW	140V	80V	1A	NPN	Die	/391
JANSR2N3019	800mW	140V	80V	1A	NPN	T0-5	/391
JANSR2N3019S	800mW	140V	80V	1A	NPN	T0-39	/391
JANSR2N3057A	500mW	140V	80V	1A	NPN	T0-46	/391
JANSR2N3439	800mW	450V	350V	1A	NPN	T0-39	/368
JANSR2N3439L	800mW	450V	350V	1A	NPN	T0-5	/368
JANSR2N3439UA	800mW	450V	350V	1A	NPN	UA	/368
JANKCBR2N3439	800mW	450V	350V	1A	NPN	Die	/368
JANSR2N3440	800mW	300V	250V	1A	NPN	T0-39	/368
JANSR2N3440L	800mW	300V	250V	1A	NPN	T0-5	/368
JANSR2N3440UA	800mW	300V	250V	1A	NPN	UA	/368
JANKCBR2N3440	800mW	300V	250V	1A	NPN	Die	/368
JANSF2N3810	350mW	60V	60V	50mA	PNP-Dual	T0-78	/336
JANSF2N3810L	350mW	60V	60V	50mA	PNP-Dual	T0-78L	/336
JANSF2N3810U	350mW	60V	60V	50mA	PNP-Dual	U	/336
JANKCAF2N3810	350mW	60V	60V	50mA	PNP-Dual	Die	/336
JANSF2N3811	350mW	60V	60V	50mA	PNP-Dual	T0-78	/336
JANSF2N3811L	350mW	60V	60V	50mA	PNP-Dual	T0-78L	/336
JANKCAF2N3811	350mW	60V	60V	50mA	PNP-Dual	T0-78L	/336
JANSF2N3811U	350mW	60V	60V	50mA	PNP-Dual	U	/336
JANSF2N5151	1W	100V	80V	2A	PNP	T0-39	/545
JANSF2N5151L	1W	100V	80V	2A	PNP	T0-5	/545
JANSF2N5151U3	1.16W	100V	80V	2A	PNP	U3	/545
JANKCCF2N5151	1W	100V	80V	2A	PNP	Die	/545
JANSF2N5153	1W	100V	80V	2A	PNP	T0-39	/545
JANSF2N5153L	1W	100V	80V	2A	PNP	T0-5	/545
JANSF2N5153U3	1.16W	100V	80V	2A	PNP	U3	/545
JANKCCF2N5153	1W	100V	80V	2A	PNP	Die	/545
JANSF2N5152	1W	100V	80V	2A	NPN	T0-39	/544
JANSF2N5152L	1W	100V	80V	2A	NPN	T0-5	/544
JANSF2N5152U3	1.16W	100V	80V	2A	NPN	U3	/544
JANKCDF2N5152	1W	100V	80V	2A	NPN	Die	/544
JANSF2N5154	1W	100V	80V	2A	NPN	T0-39	/544
JANSF2N5154L	1W	100V	80V	2A	NPN	T0-5	/544
JANSF2N5154U3	1.16W	100V	80V	2A	NPN	U3	/544
JANKCDF2N5154	1W	100V	80V	2A	NPN	Die	/544
JANSF2N5002	2W	100V	80V	5A	NPN	T0-59	/534
JANKCBF2N5002	2W	100V	80V	5A	NPN	T0-59	/534
JANSF2N5004	2W	100V	80V	5A	NPN	T0-59	/534
JANSF2N7373	4W	100V	80V	5A	NPN	T0-254AA	/613

Products are offered up to Radiation Hardness Assurance (RHA) Level F (Total ionizing dose = 300K RAD(Si) or Level R (Total ionizing dose = 100K RAD(Si) as indicated above. All lower total dose levels are also available:

RHA Prefix	Total Ionizing Dose Level
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M	3K RAD(Si)
D	10K RAD(Si)
P	30K RAD(Si)
L	50K RAD(Si)
R	100K RAD(Si)
F	300K RAD(Si)

A full description of these devices and technical data sheets are available on the Microsemi website: www.microsemi.com.

About Microsemi

Microsemi Corporation, with corporate headquarters in Irvine, California, is a leading designer, manufacturer and marketer of high performance analog and mixed-signal integrated circuits and high reliability semiconductors. The company's semiconductors manage and control or regulate power, protect against transient voltage spikes and transmit, receive and amplify signals.

Microsemi's products include individual components as well as integrated circuit solutions that enhance customer designs by improving performance and reliability, battery optimization, reducing size or protecting circuits. The principal markets the company serves include implanted medical, defense/aerospace and satellite, notebook computers, monitors and LCD TVs, automotive and mobile connectivity applications. More information may be obtained by contacting the company directly or by visiting its website at <http://www.microsemi.com>.

The Microsemi Corporation logo is available at <http://www.globenewswire.com/newsroom/prs/?pkgid=1233>

PLEASE READ THE FOLLOWING FACTORS THAT CAN MATERIALLY AFFECT MICROSEMI'S FUTURE RESULTS.

"Safe Harbor" Statement under the Private Securities Litigation Reform Act of 1995: Any statements set forth in this news release that are not entirely historical and factual in nature, including without limitation statements concerning DSCC qualification that has been granted on our JANSR2N3439 and JANSR2N3440 radiation hardened medium power transistors, are forward-looking statements. These forward-looking statements are based on our current expectations and are inherently subject to risks and uncertainties that could cause actual results to differ materially from those expressed in the forward-looking statements. The potential risks and uncertainties include, but are not limited to, such factors as rapidly changing technology and product obsolescence, potential cost increases, variations in customer order preferences, weakness or competitive pricing environment of the marketplace, uncertain demand for and acceptance of the company's products, adverse circumstances in any of our end markets, results of in-process or planned development or marketing and promotional campaigns, difficulties foreseeing future demand, potential non-realization of expected orders or non-realization of backlog, product returns, product liability, and other potential unexpected business and economic conditions or adverse changes in current or expected industry conditions, difficulties and costs of protecting patents and other proprietary rights, inventory obsolescence and difficulties regarding customer qualification of products. In addition to these factors and any other factors mentioned elsewhere in this news release, the reader should refer as well to the factors, uncertainties or risks identified in the company's most recent Form 10-K and all subsequent Form 10-Q reports filed by Microsemi with the SEC. Additional risk factors may be identified from time to time in Microsemi's future filings. The forward-looking statements included in this release speak only as of the date hereof, and Microsemi does not undertake any obligation to update these forward-looking statements to reflect subsequent events or circumstances.

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